

**IN THE CLAIMS**

This listing of claims replaces all prior listings:

1. (Currently Amended) A magnetoresistive device having:

an intermediate layer;

a fixed magnetization layer located directly below and in contact with said intermediate layer, said fixed magnetization layer is a crystalline ferromagnetic material that is made of an alloy of at least one of the following iron, nickel and cobalt; and

a free magnetization layer located adjacently above said intermediate layer, said free magnetization layer is an amorphous ferromagnetic material that is made of an alloy of at least one an iron group element and at least one element selected from the group consisting of element and metalloid elements, rare earth elements and valve metals,

wherein,

said fixed magnetization layer and said free magnetization layer are a pair of ferromagnetic layers opposed to each other to obtain variations in magnetoresistance by an electric current flowing in a direction perpendicular to the film plane,

the magnetoresistive device has a tunnel magnetic resistive (TMR) ratio greater than 45%, a coercivity value less than 6% and a rectangle ratio greater than 90%.

2. (Original) A magnetoresistive device according to claim 1, characterized in that said magnetoresistive device has a laminated ferri structure.

3. (Original) A magnetoresistive device according to claim 1, characterized in that said magnetoresistive device is a tunnel magnetoresistive device using a tunnel barrier layer

made of an insulating material or a semiconducting material as said intermediate layer.

4. (Currently Amended) A magnetic memory apparatus comprising:

a word line;

a bit line; and

a magnetoresistive device sandwiched by said word line and said bit line, said

magnetoresistive device having (1) a fixed magnetization layer located directly below and in contact with said intermediate layer, said fixed magnetization layer is a crystalline ferromagnetic material that is made of an alloy of at least one of the following iron, nickel and cobalt and (2) a free magnetization layer located adjacently above said intermediate layer, said free

magnetization layer is an amorphous ferromagnetic material that is made of an alloy of at least one an iron group element element and at least one element selected from the group consisting of metalloid elements, rare earth elements and valve metals,

wherein,

said fixed magnetization layer and said free magnetization layer are a pair of ferromagnetic layers opposed to each other to obtain variations in magnetoresistance by an electric current flowing in a direction perpendicular to the film plane,

the magnetoresistive device has a tunnel magnetic resistive (TMR) ratio greater than 45%, a coercivity value less than 6% and a rectangle ratio greater than 90%.

5. (Original) A magnetic memory apparatus according to claim 4, characterized in that said magnetoresistive device has a laminated ferri structure.

6. (Original) A magnetic memory apparatus according to claim 4, characterized in that said magnetoresistive device is a tunnel magnetoresistive device using a tunnel barrier layer made of an insulating material or a semiconducting material as said intermediate layer.